

Amendments To The Specification:

In the English translation document, please delete the term --Description-- at page 1 written line 1, before the title.

In the English translation document, please add the paragraph at page 1 after written line 3, after the title, as follows:

--CROSS REFERENCE TO RELATED APPLICATIONS

This application is the US National Stage of International Application No. PCT/DE2003/002932, filed September 3, 2003 and claims the benefit thereof. The International Application claims the benefits of German application No. 10244977.5 filed September 26, 2002, both applications are incorporated by reference herein in their entirety.--

In the English translation document, please add the paragraph at page 1 after written line 3, after the newly added CROSS REFERENCE TO RELATED APPLICATIONS section, as follows:

--FIELD OF THE INVENTION

The invention relates to the acceleration of the programming of a memory module with the aid of a Boundary Scan (BSCAN) register.--

In the English translation document, please delete the paragraph at page 1 written lines 4-12.

In the English translation document, please add the section heading at page 1 after written line 12, as follows:

-- BACKGROUND OF THE INVENTION--

In the English translation document, please amend the paragraph at page 4 written lines 14-20, as follows:

b) ~~in~~ In the last case the flash memory can be stimulated directly with the aid of an additional signal which is output via the TAP Controller defined in the IEEE 1149.1 Standard. This requires the test or programming equipment to support the control of an additional signal and an additional pin to be provided on the module for this interface embodied as a plug-in connection.

In the English translation document, please add the section heading at page 4 after written line 20, as follows:

-- SUMMARY OF THE INVENTION--

In the English translation document, please delete the line at page 4 written line 21.

In the English translation document, please delete the line at page 5 written line 10.

In the English translation document, please add the paragraphs at page 11 after written line 21, as follows:

The underlying invention is based on a method and a control unit for programming a memory module by stimulating its individual control signals, data and/or address inputs via internal memory cells of what is known as a Boundary Scan (BSCAN) register which is realized as an integrated circuit (IC or ASIC). To activate or deactivate a write operation in this case exclusively the control input responsible for the generation of a WRITE_ENABLE signal of the memory module is controlled.

The invention further comprises a control unit for programming a memory module by stimulating individual inputs of the memory module via at least one memory cell of a BSCAN register for generating a WRITE_ENABLE signal for the purposes of activating or deactivating a write operation, the control unit adapted for automatically switching the WRITE_ENABLE signal from "LOW" to "HIGH" potential or from "HIGH" to "LOW" potential by a control unit, wherein an update flip-flop of the memory cell responsible for the generation of the WRITE_ENABLE signal is set or reset.

The invention further comprises a memory cell of a BSCAN register (102), which is used when programming a memory module (104) for stimulation of individual inputs (CS, OE, WR, ADDR, DATA) of the memory module (104) for the purposes of initiating or ending a write operation, the memory cell adapted for exclusively activating a control signal input of the memory module responsible for activating or deactivating a write operation, wherein a switch-over of a WRITE_ENABLE signal fed to the control signal input by the memory cell from "LOW" to "HIGH"

potential or from "HIGH" to "LOW" potential is controlled using an instruction sequence fed to inputs of an update flip-flop of the memory cell, the update flip-flop generating the WRITE ENABLE signal having a "LOW" level or a "HIGH" level based on the instruction sequence.

The invention further comprises a memory cell of a BSCAN register (102), which is used when programming a memory module (104) for stimulation of individual inputs (CS, OE, WR, ADDR, DATA) of the memory module (104) for the purposes of initiating or ending a write operation, the memory cell adapted for automatically switching a WRITE_ENABLE signal from "LOW" to "HIGH" potential or from "HIGH" to "LOW" potential by a control unit, wherein an update flip-flop of the memory cell responsible for the generation of the WRITE_ENABLE signal is set or reset.

The invention further comprises a BSCAN register, consisting of a number of memory cells (103) for control of a programmable memory module (104), which is used for stimulation of individual inputs (CS, OE, WR, ADDR, DATA) of the memory module (104) for the purposes of initiating or ending a write operation, the BSCAN register adapted for performing a method for programming a memory module by stimulating individual inputs of the memory module via at least one memory cell of the BSCAN register by exclusively activating a control signal input of the memory module responsible for activating or deactivating a write operation, wherein a switch-over of a WRITE ENABLE signal fed to the control signal input by the memory cell from "LOW" to "HIGH" potential or from "HIGH" to "LOW" potential is controlled using an instruction sequence fed to inputs of an update flip-flop of the memory cell, the update flip-flop generating the WRITE ENABLE signal having a "LOW" level or a "HIGH" level based on the instruction sequence.

The invention further comprises a BSCAN register, consisting of a number of memory cells (103) for control of a programmable memory module (104), which is used for stimulation of individual inputs (CS, OE, WR, ADDR, DATA) of the memory module (104) for the purposes of initiating or ending a write operation, the BSCAN register adapted for performing a method for programming a memory module by stimulating individual inputs of the memory module via at least one memory cell of the BSCAN register for generating a WRITE_ENABLE signal for the purposes of activating or deactivating a write operation, by automatically switching the

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WRITE_ENABLE signal from "LOW" to "HIGH" potential or from "HIGH" to "LOW" potential by a control unit, wherein an update flip-flop of the memory cell responsible for the generation of the WRITE_ENABLE signal is set or reset.